

ABSTRACT OF THE DISCLOSURE

A semiconductor device comprises a semiconductor substrate, an N-channel MISFET and a P-channel MISFET provided on the semiconductor substrate, each of the N-
5 and P-channel MISFETs being isolated by an isolation region and having a gate insulating film, a first gate electrode film provided on the gate insulating film of the N-channel MISFET and composed of a first metal silicide, a second gate electrode film provided on the
10 gate insulating film of the P-channel MISFET and composed of a second metal silicide made of a second metal material different from a first metal material composing the first metal silicide, and a work function of the first gate electrode film being lower than that
15 of the second gate electrode film.